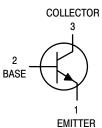
Amplifier Transistor NPN Silicon

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	120	Vdc
Collector-Base Voltage	V _{CBO}	140	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current — Continuous	۱ _C	150	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C





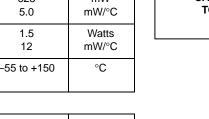
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	R_{\thetaJA}	200	°C/W
Thermal Resistance, Junction to Case	$R_{ extsf{ heta}JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage ⁽¹⁾ ($I_c = 1.0$ mAdc, $I_B = 0$)	V _{(BR)CEO}	120	—	Vdc
Collector–Base Breakdown Voltage $(I_C = 100 \ \mu Adc, I_E = 0)$	V _{(BR)CBO}	140	—	Vdc
Emitter–Base Breakdown Voltage $(I_E = 10 \ \mu Adc, I_C = 0)$	V _{(BR)EBO}	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 75 \text{ Vdc}, I_E = 0$)	I _{CBO}	—	1.0	μAdc
Emitter Cutoff Current ($V_{EB} = 4.0 \text{ Vdc}, I_C = 0$)	I _{EBO}		100	nAdc

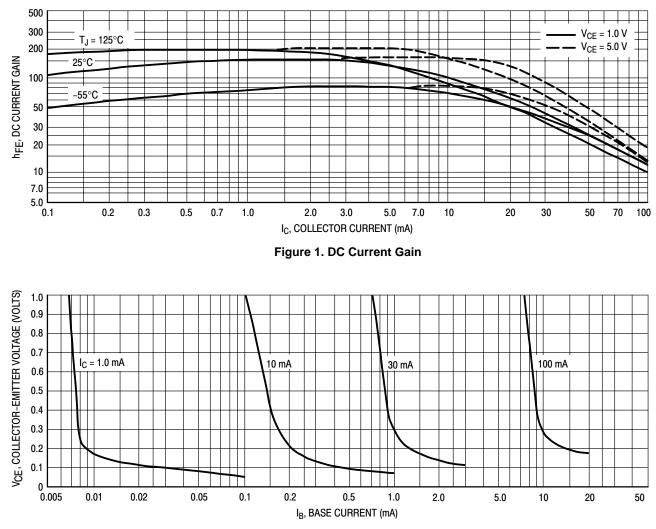
1. Pulse Test: Pulse Width = $300 \ \mu s$, Duty Cycle = 2.0%.



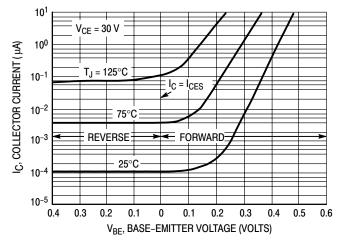
MPSL01

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain ⁽¹⁾ (I _C = 10 mAdc, V _{CE} = 5.0 Vdc)	h _{FE}	50	300	—
Collector–Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc}$)	V _{CE(sat)}	_	0.20 0.30	Vdc
Base–Emitter Saturation Voltage $(I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc})$ $(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})^{(1)}$	V _{BE(sat)}	_	1.2 1.4	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current–Gain — Bandwidth Product ⁽¹⁾ ($I_c = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 20 \text{ MHz}$)	fT	60	—	MHz
Collector–Base Capacitance (V_{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	C _{cb}	_	8.0	pF
Small–Signal Current Gain (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{fe}	30	_	_

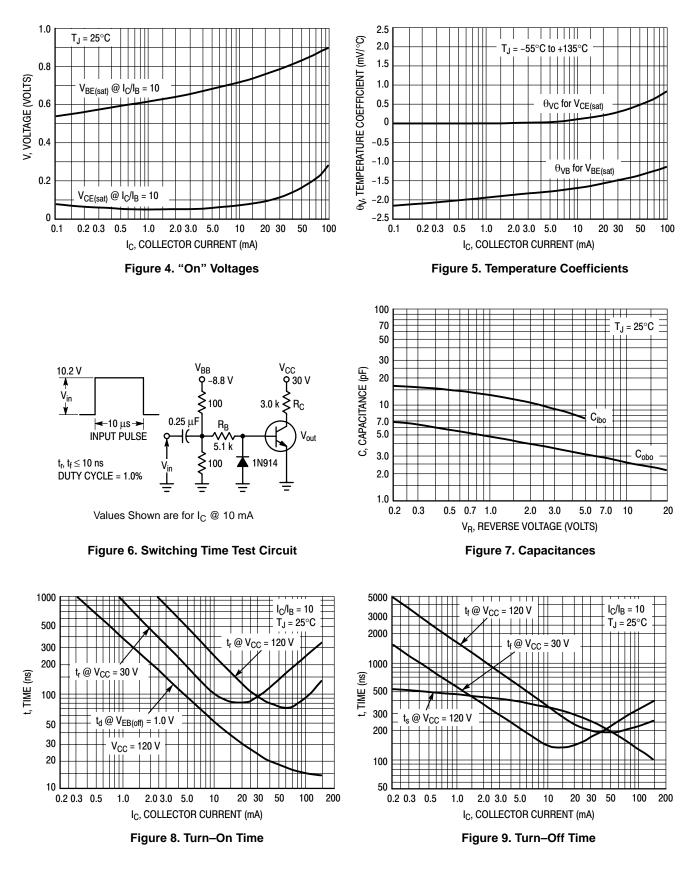
1. Pulse Test: Pulse Width = 300 $\mu s,$ Duty Cycle = 2.0%.





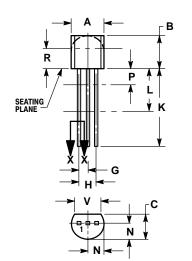






PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AL





NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED. 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
К	0.500		12.70	
L	0.250		6.35	
Ν	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

<u>Notes</u>

<u>Notes</u>

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